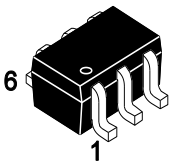
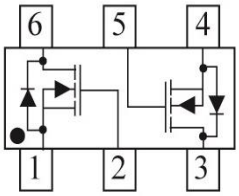
LBSS138DW1T1G
S-LBSS138DW1T1G

Power MOSFET
200 mAmps, 50 Volts N–Channel SC-88



SC88(SOT-363)



1. FEATURES

- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- S- prefix for automotive and other applications requiring unique site and control change requirements; AEC-Q101 qualified and PPAP capable.
- Low threshold voltage (VGS(th): 0.5V...1.5V) makes it ideal for low voltage applications.

2. DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
LBSS138DW1T1G	J1	3000/Tape&Reel
LBSS138DW1T3G	J1	10000/Tape&Reel

3. MAXIMUM RATINGS(Ta = 25ºC)

Parameter	Symbol	Limits	Unit
Drain–Source Voltage	VDSS	50	Vdc
Gate–to–Source Voltage – Continuous	VGS	±20	Vdc
Drain Current – Continuous TA = 25°C – Pulsed (tp≤10μs)	 ID IDM	 200 800	mAdc

4. THERMAL CHARACTERISTICS

Parameter	Symbol	Limits	Unit
Total Device Dissipation, FR−5 Board (Note 1) @ TA = 25ºC Derate above 25ºC	PD	225 1.8	mW mW/ºC
Thermal Resistance, Junction–to–Ambient(Note 1)	RΘJA	556	ºC/W
Junction and Storage temperature	TJ,Tstg	−55~+150	°C
Maximum Lead Temperature for Solde Purposes, for 10 seconds	TL	260	ºC

1. FR–5 = 1.0×0.75×0.062 in.

5. ELECTRICAL CHARACTERISTICS (Ta= 25°C)

OFF CHARACTERISTICS

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Drain–Source Breakdown Voltage (VGS = 0, ID = 250μAdc)	VBRDSS	50	-	-	Vdc
Zero Gate Voltage Drain Current (VGS = 0, VDS = 25 Vdc) (VGS = 0, VDS = 50 Vdc)	IDSS	- -	- -	0.1 0.5	μAdc
Gate–Body Leakage Current, Forward (VGS = 20 Vdc)	IGSSF	-	-	0.1	μAdc
Gate–Body Leakage Current, Reverse (VGS = - 20 Vdc)	IGSSR	-	-	-0.1	μAdc

ON CHARACTERISTICS (Note 2)

Gate Threshold Voltage (VDS = VGS, ID = 1.0mAdc)	VGS(th)	0.5	-	1.5	Vdc
Static Drain–Source On–State Resistance (VGS = 2.75 Vdc, ID < 200 mAdc, TA = –40°C to +85°C) (VGS = 5.0 Vdc, ID = 200 mAdc)	RDS(on)	- -	5.6 -	10 3.5	Ohms
Forward Transconductance (VDS = 25 Vdc, ID = 200 mAdc, f = 1.0 kHz)	gfs	100	-	-	mS

DYNAMIC CHARACTERISTICS

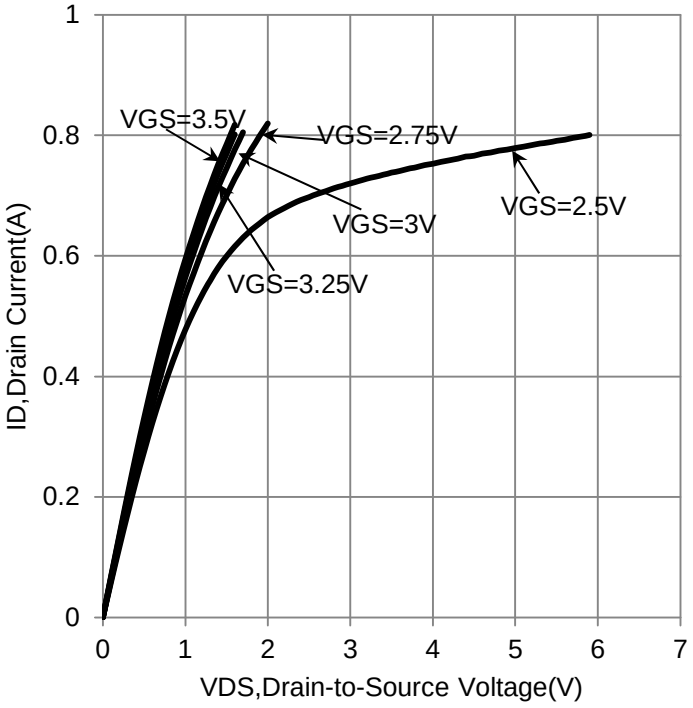
Input Capacitance (VDS = 25 Vdc, VGS = 0, f = 1.0 MHz)	Ciss	-	40	50	pF
Output Capacitance (VDS = 25 Vdc, VGS = 0, f = 1.0 MHz)	Coss	-	12	25	pF
Reverse Transfer Capacitance (VDS = 25 Vdc, VGS = 0, f = 1.0 MHz)	Ciss	-	3.5	5.0	pF

SWITCHING CHARACTERISTICS

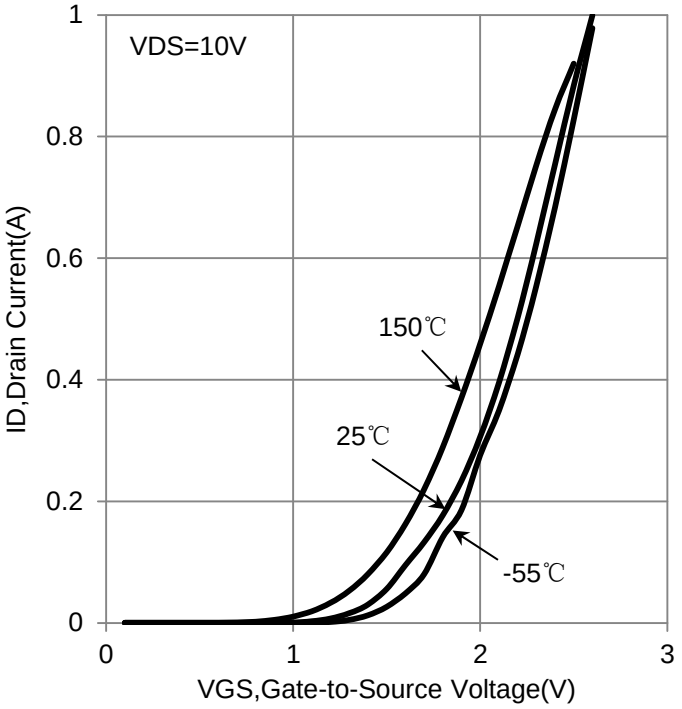
Turn-On Delay Time	(VDD = 30 Vdc , ID =200 mAdc)	td(on)	-	-	20	ns
Turn-Off Delay Time		td(off)	-	-	20	

2.Pulse Test: Pulse Width ≤300 μs, Duty Cycle ≤2.0%.

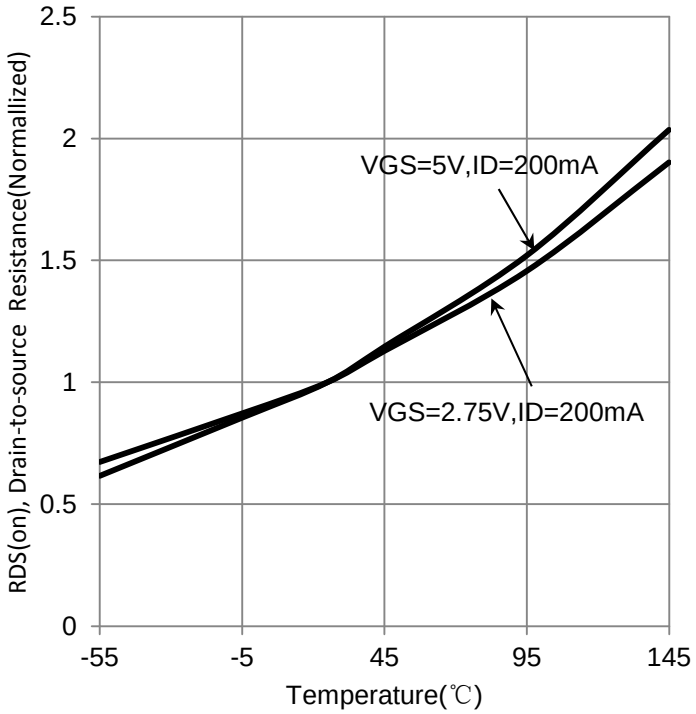
6. ELECTRICAL CHARACTERISTICS CURVES



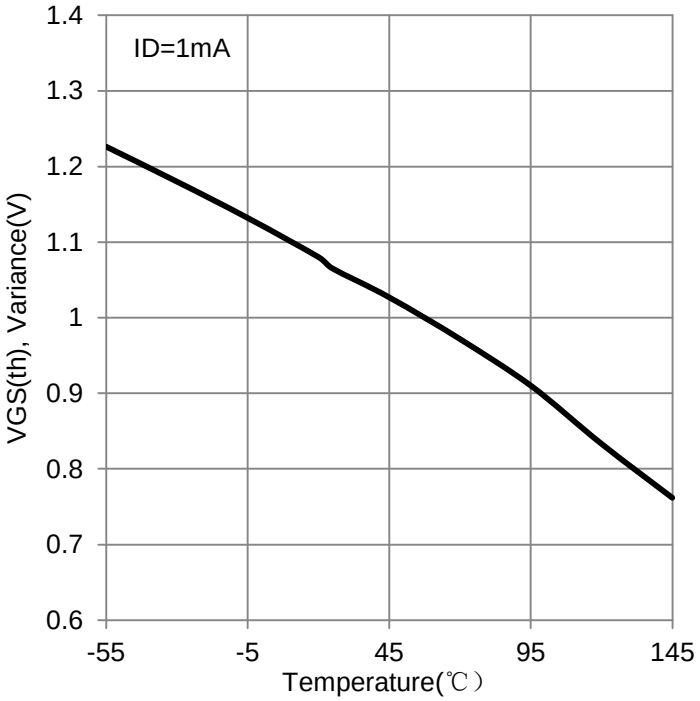
On-Region Characteristics



Transfer Characteristics

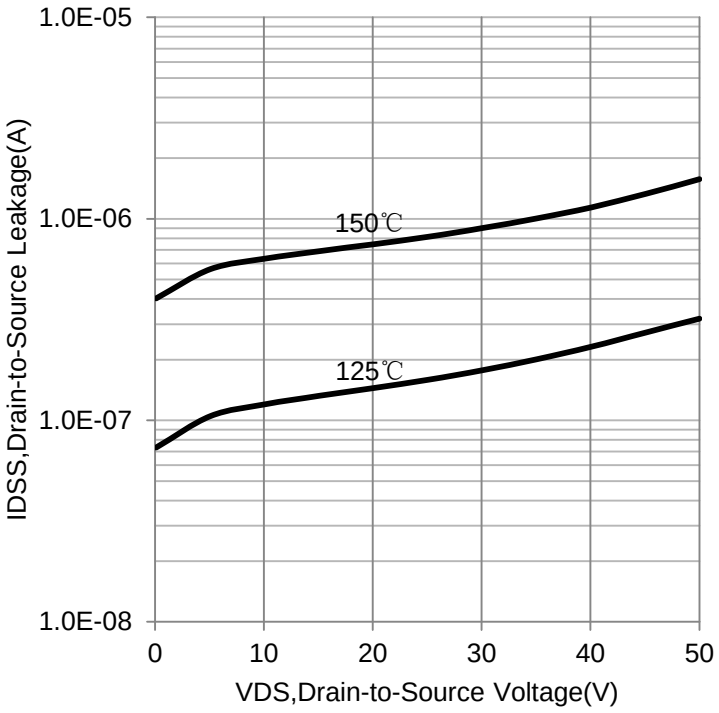


RDS(on) vs. Temperature

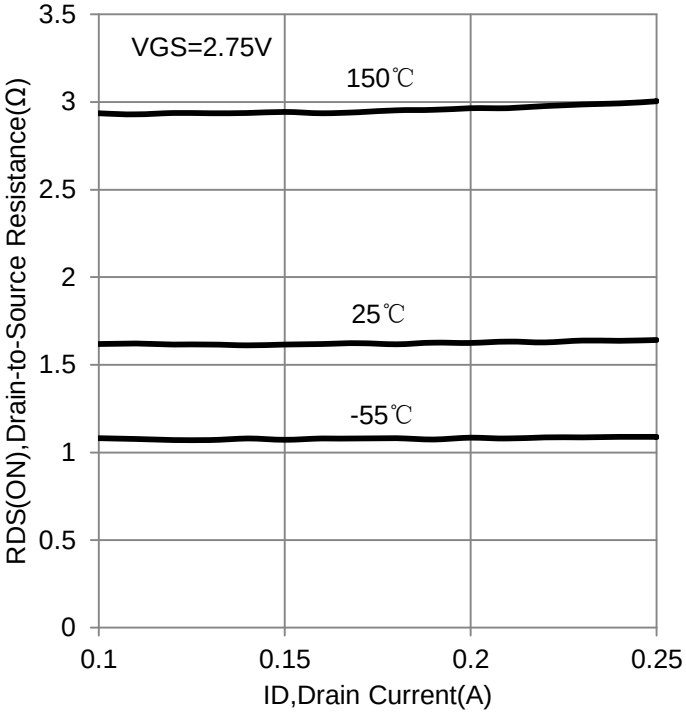


Threshold Voltage vs.Temperature

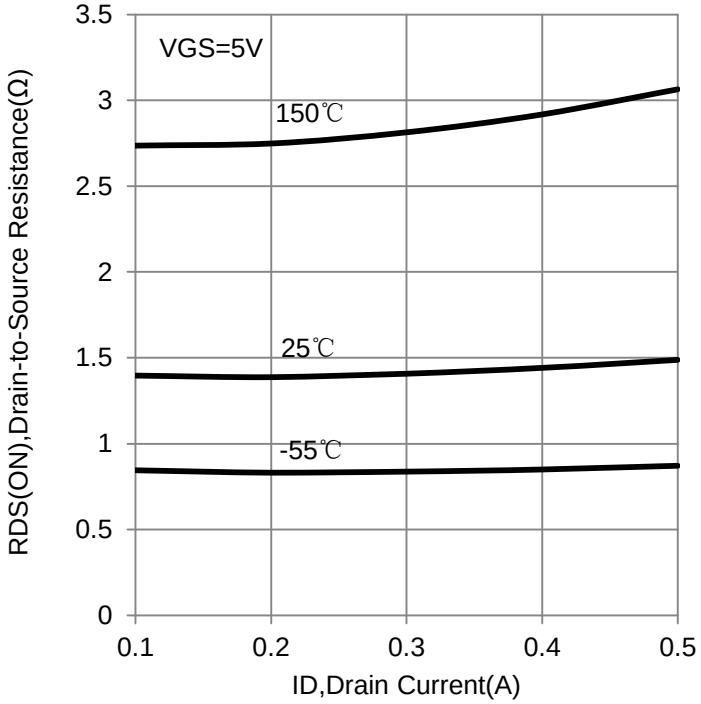
6.ELECTRICAL CHARACTERISTICS CURVES(Con.)



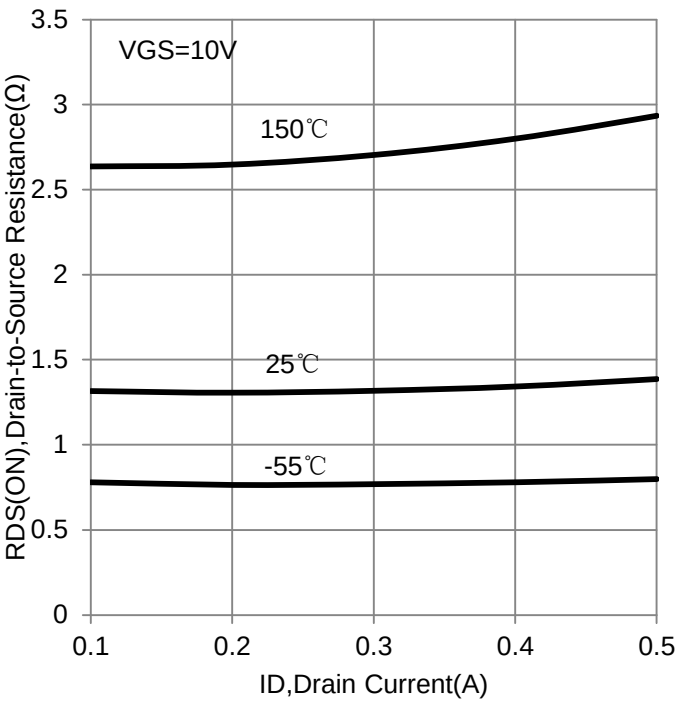
IDSS vs. VDS



RDS(on) vs. ID

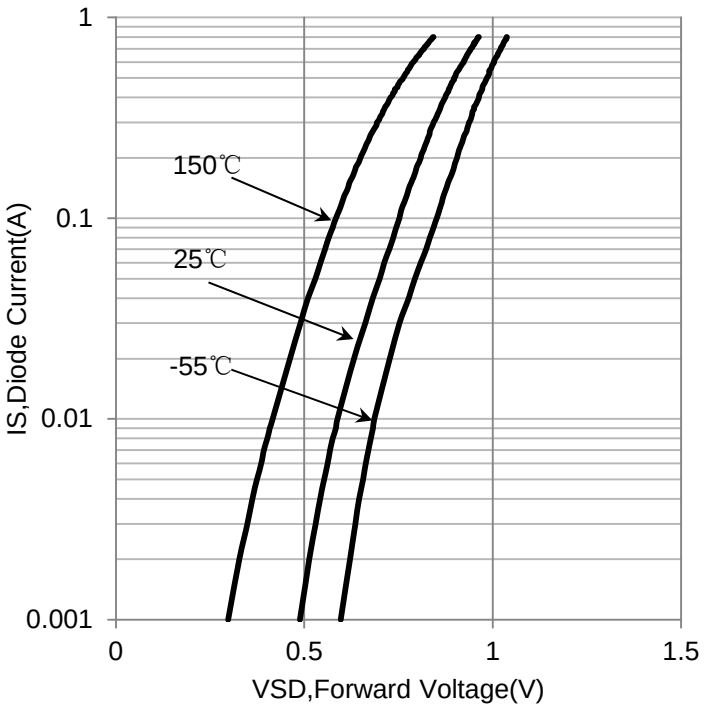


RDS(on) vs. ID

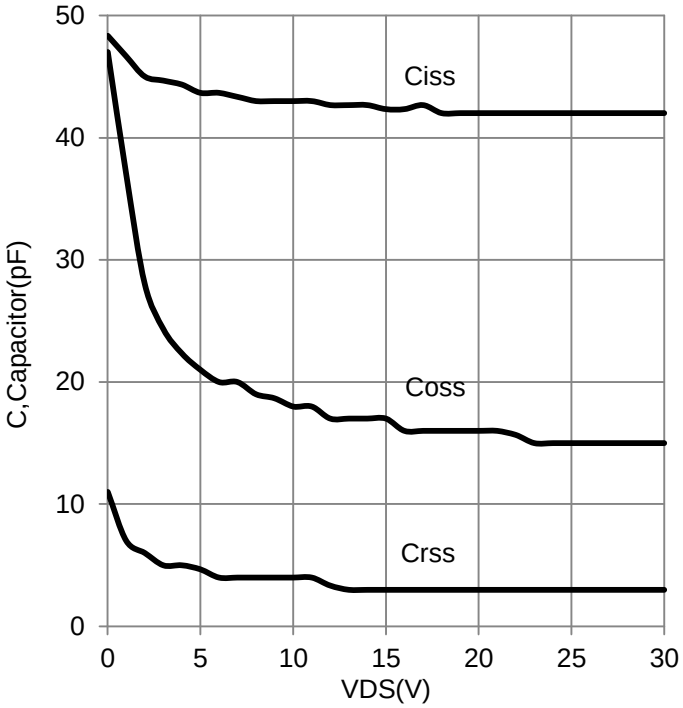


RDS(on) vs. ID

6.ELECTRICAL CHARACTERISTICS CURVES(Con.)

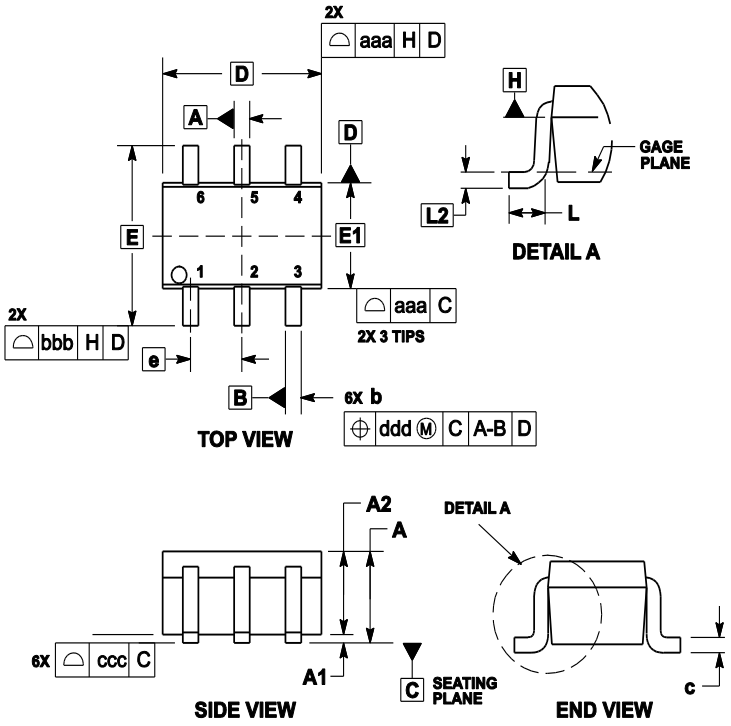


Body Diode Forward Voltage



Capacitor vs.VDS

7.OUTLINE AND DIMENSIONS



Notes:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	---	---	1.10	---	---	0.043
A1	0.00	---	0.10	0	---	0.004
A2	0.70	0.90	1.00	0.027	0.035	0.039
b	0.15	0.20	0.25	0.006	0.008	0.01
C	0.08	0.15	0.22	0.003	0.006	0.009
D	1.80	2.00	2.20	0.07	0.078	0.086
E	2.00	2.10	2.20	0.078	0.082	0.086
E1	1.15	1.25	1.35	0.045	0.049	0.053
e	0.65 BSC			0.026 BSC		
L	0.26	0.36	0.46	0.010	0.014	0.018
L2	0.15 BSC			0.006 BSC		
aaa	0.15			0.01		
bbb	0.30			0.01		
ccc	0.10			0.00		
ddd	0.10			0.00		

8.SOLDERING FOOTPRINT